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PATENT
465-758P

John H

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Jun S. LEE Conf.: 5244
Serial No.: 09/722,583 Art Unit: 2823
Filed: November 28, 2000 Examiner: B. Kebede
For: METHOD FOR FABRICATING CAPACITOR OF
SEMICONDUCTOR DEVICE

RECEIVED
TECHNOLOGY CENTER 2800
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AMENDMENT UNDER 37 C.F.R. §1.111

Assistant Commissioner for Patents
Washington, DC 20231

February 5, 2003

Sir:

In response to the Office Action mailed November 7, 2002 (Paper No. 14),
the following amendments and remarks are respectfully submitted in

~~connection with the above~~ application:

02/12/2003 A5MAY 001 84.00 CH
01 FC:1201

IN THE CLAIMS:

Please **rewrite claims 1 and 4** as follows:

1. (Amended) A method for fabricating a capacitor of a semiconductor device comprising:

depositing a nitride film and an oxide film over a substrate, the oxide film being deposited on the nitride film by chemical vapor deposition;

sequentially etching the oxide film and the nitride film using a patterned photoresist as a mask;

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